Signal Conditioning and Linearization of RTD Sensors

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Introduction

- Primary Support
 - 4-20mA Loop Drivers (XTRXXX)
 - Gamma Buffers (BUFXXXXX)
- Other Support
 - Temperature Sensors (TMP)
 - IR Temperature Sensors (TMP006)
 - OPA Stability
 - Instrument Amplifiers
- Applications (Other)
 - Industrial Programmable Logic Controllers (PLC)
 - RTD
 - Reference Designs





Contents

- RTD Overview
- •RTD Nonlinearity
- Analog Linearization
- •Digital Acquisition and Linearization



What is an RTD?

- <u>Resistive Temperature Detector</u>
- Sensor with a predictable resistance vs. temperature
- Measure the resistance and calculate temperature based on the Resistance vs. Temperature characteristics of the RTD material



How does an RTD work?

Resistance = R =
$$\frac{\rho \cdot L}{A}$$

Resistivity = p = $\frac{1}{e \cdot n \cdot \mu}$

- L = Wire Length
- A = Wire Area
- e = Electron Charge (1.6e-19 Coulombs)
- n = Electron Density
- u = Electron Mobility
- The product n*u decreases over temperature, therefore resistance increases over temperature (PTC)
- Linear Model of Conductor Resistivity Change vs. Temperature

$$\rho(t) = \rho_0 (1 + \alpha (t - t_0))$$



What is an RTD made of?

- Platinum (pt)
- Nickel (Ni)
- Copper (Cu)

Have relatively linear change in resistance over temp
Have high resistivity allowing for smaller dimensions
Either Thin-Film or Wire-Wound



Figure 1. The coiled element sensor, made by inserting the helical sensing wires into a packed powderfilled insulating mandrel, provides a strain-free sensing element. MetalResistivity
(Ohm/CMF)Gold (Au)13Silver (Ag)8.8Copper (Cu)9.26Platinum (Pt)59Tungsten (W)30Nickel (Ni)36



Figure 2. The thin film sensing element is made by depositing a thin layer of platinum in a resistance pattern on a ceramic substrate. A glassy layer is applied for seal and protection.

*Images from RDF Corp



How Accurate is an RTD?

• Absolute accuracy is "Class" dependant - defined by DIN-IEC 60751. Allows for easy interchangeability of field sensors

	**Temperature Range of Validity				Error at	Error over Wire-
Tolerance Class (DIN-IEC 60751)	Wire- Wound	Thin-Film	Tolerance Values (C)	Resistance at 0C (Ohms)	100C (C)	Wound Range (C)
*AAA (1/10 DIN)	0 - +100	0 - +100	+/-(0.03 + 0.0005*t)	100 +/- 0.012	0.08	0.08
AA (1/3DIN)	-50 - +250	0 - +150	+/-(0.1 + 0.0017*t)	100 +/- 0.04	0.27	0.525
A	-100 - +450	-30 - +300	+/-(0.15 + 0.002*t)	100 +/- 0.06	0.35	1.05
В	-196 - +600	-50 - +500	+/-(0.3 + 0.005*t)	100 +/- 0.12	0.8	3.3
С	-196 - +600	-50 - +600	+/-(0.6 + 0.01*t)	100 +/- 0.24	1.6	6.6

*AAA (1/10DIN) is not included in the DIN-IEC-60751 spec but is an industry accepted tolerance class for high-performance measurements

**Manufacturers may choose to guarantee operation over a wider temperature range than the DIN-IEC60751 provides

- Repeatability usually very good, allows for individual sensor calibration
- Long-Term Drift usually <0.1C/year, can get as low as 0.0025C/year



Why use an RTD?

Table Comparing Advantages and Disadvantages of Temp Sensors





How to Measure an RTD Resistance?

• Use a.....





Simple Current Source / Sink Circuits



RTD Types and Their Parasitic Lead Resistances



2-Wire Measurements





$$V_{\text{meas}} = I_{\text{source}} \cdot R_{\text{RTD}} + I_{\text{source}} \cdot 2 \cdot R_{\text{L}}$$

Error =
$$I_{\text{source}} \cdot 2R_{\text{L}}$$

$$V_{\text{meas}} = V_{\text{source}} \cdot \left[\left(\frac{R_{\text{RTD}} + 2R_{\text{L}}}{R_{\text{A}} + R_{\text{RTD}} + 2R_{\text{L}}} \right) - \frac{1}{2} \right]$$

Error = $V_{\text{source}} \left[\frac{2 \cdot R_{\text{A}} \cdot R_{\text{L}}}{(R_{\text{A}} + R_{\text{RTD}}) \cdot (R_{\text{A}} + 2 \cdot R_{\text{L}} + R_{\text{RTD}})} \right]$



3-Wire Measurements



Error = 0 as long as Isource1 = Isource2 and RL are equal



4-Wire Measurements



Self-Heating Errors of RTD

- Typically 2.5mW/C 60mW/C
- Set excitation level so self-heating error is <10% of the total error budget



Self-Heating Error of an RTD vs. Exciation Current

NSTRUMENTS

RTD Resistance vs Temperature



RTD Nonlinearity



RTD Nonlinearity

For (T > 0):
$$\operatorname{RTD}(T) := \operatorname{R}_{0} \cdot \left[1 + \operatorname{A} \cdot T + \operatorname{B} \cdot \left(\operatorname{T}^{2} \right) \right]$$

For (T < 0): $\operatorname{RTD}(T) := \operatorname{R}_{0} \cdot \left[1 + \operatorname{A} \cdot T + \operatorname{B} \cdot \left(\operatorname{T}^{2} \right) + \operatorname{C} \cdot \left(\operatorname{T}^{3} \right) \cdot \left(\operatorname{T} - 100 \right) \right]$

$$\mathrm{RTD}_{\mathrm{linear}}(\mathrm{T}) \coloneqq \mathrm{R}_{\mathrm{0}} \cdot (1 + \mathrm{A} \cdot \mathrm{T})$$







Correcting for Non-Linearity

Sensor output decreases over span? Compensate by increasing excitation over span!



Correcting for Non-linearity

 $I_{source} := 0.0005$

 $V_{\text{RTD}}(T) \coloneqq \text{RTD}(T) \cdot I_{\text{source}}$

$$I_{source_correction}(T) \coloneqq I_{source} + \frac{\left(V_{RTD_linear}(T) - V_{RTD}(T)\right)}{RTD(T)}$$

$$V_{\text{RTD}_\text{correction}}(T) \coloneqq \text{RTD}_{\text{linear}}(T) \cdot I_{\text{source}_\text{correction}}(T)$$

 $V_{\text{RTD_linear}}(T) := \text{RTD}_{\text{linear}}(T) \cdot I_{\text{source}}$

 $V_{\text{RTD_linearized}}(T) := I_{\text{source_correction}}(T) \cdot \text{RTD}(T)$





Two-Wire Single Op-Amp

Example Amplifiers:

OPA333 OPA376

Low-Voltage:



High Voltage: OPA188 OPA277

This circuit is designed for a 0-5V output for a 0-200C temperature span. Components R2, R3, R4, and R5 are adjusted to change the desired measurement temperature span and output.



Two-Wire Single Op-Amp

Non-linear increase in excitation current over temperature span will help correct non-linearity of RTD measurement









TEXAS

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XTR105 4-20mA Current Loop Output



XTR105 4-20mA Current Loop Output



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Digital Acquisition Circuits and Linearization Methods



ADS1118 16-bit Delta-Sigma 2-Wire Measurement with Half-Bridge





ADS1220 24-bit Delta-Sigma Two 3-wire RTDs





ADS1220 24-bit Delta-Sigma One 4-Wire RTD



ADS1247 24-bit Delta-Sigma Three-Wire + Rcomp



Note: R_{BIAS} and R_{COMP} should be as close to the ADC as possible.



ADS1247 24-bit Delta-Sigma Four-Wire



Note: R_{BIAS} should be as close to the ADC as possible.



- Three main options
 - Linear-Fit
 - Piece-wise Linear Approximations
 - Direct Computations





Linear Fit

Pro's:

•Easiest to implement

Con's:

Least Accurate

- •Very Fast Processing Time
- •Fairly accurate over small temp span



Piece-wise Linear Fit

Pro's:

- •Easy to implement
- •Fast Processing Time
- •Programmable accuracy

Con's:

•Code size required for coefficients

$$T_{\text{Peicewise}} = T(n-1) + (T(n) - T(n-1)) \left(\frac{RTD - RTD(n-1)}{RTD(n) - RTD(n-1)} \right)$$



Direct Computation

Pro's:

- •Almost Exact Answer, Least Error
- •With 32-Bit Math Accuracy to +/-0.0001C

Con's:

- Processor intensive
- •Requires Math Libraries

•Negative Calculation Requires simplification or bi-sectional solving





Direct Computation

Bi-Section Method for Negative Temperatures

RTDError = 100Res := 60.256 Tlow := -250Thigh = 50 $T_{\text{Bisection}} := \left[\text{RTDTemp} \leftarrow 0 \right]$ = -99.999while (|RTDError| > 0.0001) $Tmid \leftarrow \frac{(Tlow + Thigh)}{2}$ $\text{Rcal} \leftarrow 100 \left[1 + \text{A} \cdot \text{Tmid} + \text{B} \text{Tmid}^2 + (\text{Tmid} - 100) \cdot \text{C} \cdot \text{Tmid}^3 \right]$ if Tmid < 0Rcal $\leftarrow 100 \left(1 + \text{A} \cdot \text{Tmid} + \text{B} \cdot \text{Tmid}^2 \right)$ if Tmid > 0 Rcal $\leftarrow 0$ if Rcal < 0RTDError \leftarrow Res – Rcal The the Tmid if RTDError > 0Thigh \leftarrow Tmid if RTDError < 0RTDTemp \leftarrow Tmid return RTDTemp

 $T_{\text{Bisection}} = -99.999$



Questions/Comments?

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